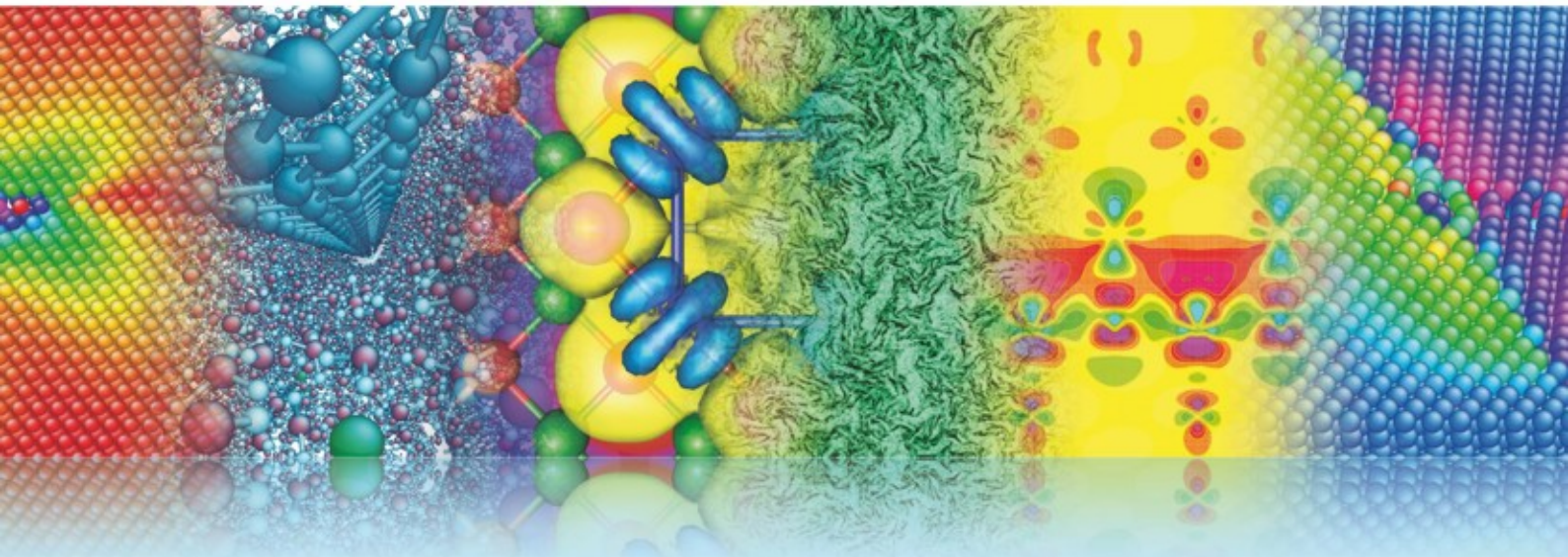


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# Reconstruction of dislocations in interface layer Cu-Al<sub>2</sub>O<sub>3</sub>

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## ABSTRACT

Using three different methods namely, CDT (Continuous Dislocation Theory), molecular TB-SMA (Tight Binding Second Moment Approximation) type many-body potential, and MEM (Molecular Effective Medium) theory, we are looking for the best possible reconstruction of dislocations in Cu-Al<sub>2</sub>O<sub>3</sub> heterostructure.

## 1. Introduction

The issue of assessing the strength and functionality of heterostructures metal - ceramic is very important both from a cognitive, as well as from a practical point-of-view.

An important, often decisive factor is knowledge of the limit state in the transitional metal – ceramic layer (interface) .

The subject of our modeling is the mismatch dislocation structure - such as those formed in the case of crystal growth of copper on the surface of sapphire (Al<sub>2</sub>O<sub>3</sub> ).

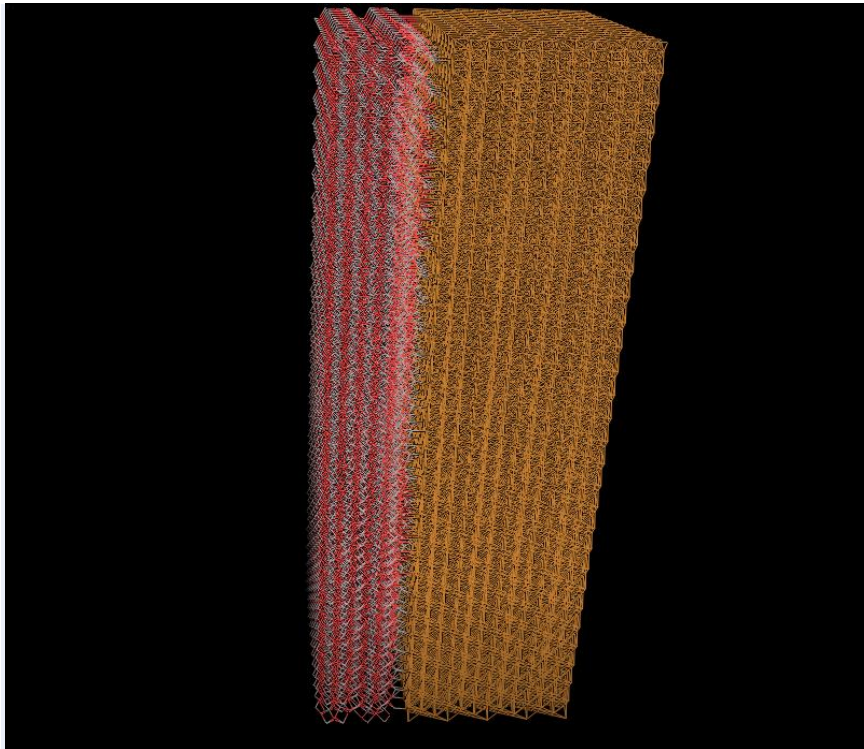


Fig.1. Copper on the surface of sapphire (Al<sub>2</sub>O<sub>3</sub> )

On the basis of existing experimental research conducted by high-resolution transmission electron microscopy (HRTEM) there is some knowledge available about the system of dislocations resulting from the mismatch between sapphire and copper [1].

We want to reconstruct the system of dislocations in the interface using various methods and compare the results. These methods are:

-Algorithm from Continuous Dislocation Theory based on newly derived analytical models for the insertion of dislocations to the continuum [2,3].

-Atomic method based on the model TB-SMA type many-body potential [1,4,5,6].

- Atomic method based on the original atomic model, in which the interaction occurring inside the layers of the Cu- Al<sub>2</sub>O<sub>3</sub> interface will be formulated in accordance with the concept of the method of Effective Medium Theory [7,8].

## 2. The methods

### 2.1 Continuous Dislocation Theory - analytical equations for mixed straight dislocation

The displacement field around a mixed straight-line dislocation in an elastic material is defined by the classical formulas [2,3]

$$\begin{aligned}
 u_x &= \frac{b_x}{2\pi} \left( \arctan \frac{y}{x} + \frac{xy}{2(1-\nu)(x^2+y^2)} \right) - \frac{b_x}{2} \\
 u_y &= -\frac{b_x}{2\pi} \left( \frac{1-2\nu}{4(1-\nu)} \ln(x^2+y^2) + \frac{x^2-y^2}{4(1-\nu)(x^2+y^2)} \right) \\
 u_z &= \frac{b_z}{2\pi} \arctan \frac{y}{x} - \frac{b_z}{2}
 \end{aligned} \tag{1}$$

where the edge and screw components of the Burgers vector , $b_x$  and  $b_z$ , are parallel to the  $x$  and  $z$  axes, respectively. Using the analytical equations of displacement field induced by discrete dislocations Eqn.1 we introduced dislocations into Cu- Al<sub>2</sub>O<sub>3</sub> structure.

### 2.2. Tight-binding second moment approximation type many-body potential

In the TB-SMA approach [1,4,5,6] potential energy per atom is a sum of the repulsive energy  $E_{rep}$ , and the binding energy  $E_b$ :

$$E_{rep} = A \sum_i \exp \left( -p \left( \frac{r_i}{r_0} - 1 \right) \right) \tag{2}$$

$$E_b = -\xi \sqrt{\sum_i \exp\left(-2q\left(\frac{r_i}{r_0} - 1\right)\right)}$$

where  $r_0$  is the distance between nearest neighbours at zero temperature and  $r_i$  is the distance of  $i$  atom from the considered one,  $A$ ;  $p$ ,  $\xi$  and  $q$  are free parameters. Parameters are identified by elastic eigen-states approach [8] and differ from the values assumed by Dimitriev [1] but better reproduce energy density of the ideal crystal.

### 2.3 Potential based on Effective Medium Theory

Using Effective Medium Theory [7] we formulated original embedded-atom method (EAM) potential for Cu-Al<sub>2</sub>O<sub>3</sub>. The covalent and metallic interactions occurring in the ceramic layer and metal layer are described correspondingly:

$$E_n = \sum_{i=1}^N F_i(\rho_i) + \frac{1}{2} \sum_{i=1}^N \sum_{j=1}^N \Phi_{ij}(r_{ij}) \quad (3)$$

The function  $F_i$  is the energy of embedding of the  $i$ -th atom in the electron density  $\rho_i$  and  $\Phi_{ij}$  is the energy of interaction of pair of atoms. EAM potential can be treated as a more flexible generalization of TB-SMA approach. To parameterize above potential elastic eigen-states approach was used with two kinds of tensile tests: so called relaxed tensile test, the sample cut off from the surroundings of the interface is being stretched in the direction normal to the interface and so called rigid tensile test.

### 3. Conclusions

We presented three methods of the reconstruction of dislocations in Cu-Al<sub>2</sub>O<sub>3</sub> heterostructure. First, the analytical one, where equations of displacement field induced by discrete dislocations are used. Next two utilize molecular approach and respectively are based on tight-binding second moment approximation potential and embedded-atom potential.

Using these methods, a relaxed structure with minimal energy will be further chosen for nanoindentation simulation in which the behaviour of the dislocation structure if nonequilibrium configuration is investigated.

### Acknowledgments

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